# Wen-Hao Chang

## List of Publications by Citations



| | | | |
|---|---|---|---|
| 160 papers | 6,977 citations | 35 h-index | 81 g-index |
| 185 ext. papers | 8,133 ext. citations | 6.7 avg, IF | 5.57 L-index |

| # | Paper | IF | Citations |
|---|---|---|---|
| 160 | NANOELECTRONICS. Epitaxial growth of a monolayer WSe2-MoS2 lateral p-n junction with an atomically sharp interface. *Science*, **2015**, 349, 524-8 | 33.3 | 811 |
| 159 | Large-area synthesis of highly crystalline WSe(2) monolayers and device applications. *ACS Nano*, **2014**, 8, 923-30 | 16.7 | 732 |
| 158 | Plasmonic nanolaser using epitaxially grown silver film. *Science*, **2012**, 337, 450-3 | 33.3 | 571 |
| 157 | Monolayer MoSe2 grown by chemical vapor deposition for fast photodetection. *ACS Nano*, **2014**, 8, 8582-90 | 16.7 | 413 |
| 156 | Second harmonic generation from artificially stacked transition metal dichalcogenide twisted bilayers. *ACS Nano*, **2014**, 8, 2951-8 | 16.7 | 294 |
| 155 | Bandgap tunability at single-layer molybdenum disulphide grain boundaries. *Nature Communications*, **2015**, 6, 6298 | 17.4 | 291 |
| 154 | Spectroscopic signatures for interlayer coupling in MoS2-WSe2 van der Waals stacking. *ACS Nano*, **2014**, 8, 9649-56 | 16.7 | 233 |
| 153 | Efficient single-photon sources based on low-density quantum dots in photonic-crystal nanocavities. *Physical Review Letters*, **2006**, 96, 117401 | 7.4 | 212 |
| 152 | Wafer-scale single-crystal hexagonal boron nitride monolayers on Cu′(111). *Nature*, **2020**, 579, 219-223 | 50.4 | 209 |
| 151 | All-color plasmonic nanolasers with ultralow thresholds: autotuning mechanism for single-mode lasing. *Nano Letters*, **2014**, 14, 4381-8 | 11.5 | 168 |
| 150 | Photoluminescence Enhancement and Structure Repairing of Monolayer MoSe2 by Hydrohalic Acid Treatment. *ACS Nano*, **2016**, 10, 1454-61 | 16.7 | 137 |
| 149 | Multidirection Piezoelectricity in Mono- and Multilayered Hexagonal □nSe. *ACS Nano*, **2018**, 12, 4976-4983 | 16.7 | 133 |
| 148 | Room-Temperature Ferroelectricity in Hexagonally Layered □n2Se3 Nanoflakes down to the Monolayer Limit. *Advanced Functional Materials*, **2018**, 28, 1803738 | 15.6 | 127 |
| 147 | Heteroepitaxial growth of wurtzite InN films on Si(111) exhibiting strong near-infrared photoluminescence at room temperature. *Applied Physics Letters*, **2004**, 84, 3765-3767 | 3.4 | 123 |
| 146 | Optically initialized robust valley-polarized holes in monolayer WSe2. *Nature Communications*, **2015**, 6, 8963 | 17.4 | 120 |
| 145 | Layered MoS2 grown on c -sapphire by pulsed laser deposition. *Physica Status Solidi - Rapid Research Letters*, **2015**, 9, 187-191 | 2.5 | 99 |
| 144 | Band gap-tunable molybdenum sulfide selenide monolayer alloy. *Small*, **2014**, 10, 2589-94 | 11 | 92 |

| | | | |
|---|---|---|---|
| 143 | Purely in-plane ferroelectricity in monolayer SnS at room temperature. *Nature Communications*, **2020**, 11, 2428 | 17.4 | 88 |
| 142 | Photocurrent studies of the carrier escape process from InAs self-assembled quantum dots. *Physical Review B*, **2000**, 62, 6959-6962 | 3.3 | 77 |
| 141 | Evidence of indirect gap in monolayer WSe. *Nature Communications*, **2017**, 8, 929 | 17.4 | 72 |
| 140 | Tuning the energy levels of self-assembled InAs quantum dots by rapid thermal annealing. *Applied Physics Letters*, **2000**, 76, 691-693 | 3.4 | 72 |
| 139 | Controllable Synthesis of Band-Gap-Tunable and Monolayer Transition-Metal Dichalcogenide Alloys. *Frontiers in Energy Research*, **2014**, 2, | 3.8 | 70 |
| 138 | Negative circular polarization emissions from WSe/MoSe commensurate heterobilayers. *Nature Communications*, **2018**, 9, 1356 | 17.4 | 61 |
| 137 | Direct measurement of piezoelectric field in In0.23Ga0.77N/GaN multiple quantum wells by electrotransmission spectroscopy. *Journal of Applied Physics*, **2002**, 91, 531 | 2.5 | 56 |
| 136 | Band Alignment of 2D Transition Metal Dichalcogenide Heterojunctions. *Advanced Functional Materials*, **2017**, 27, 1603756 | 15.6 | 55 |
| 135 | Room-temperature electroluminescence at 1.3 and 1.5 μm from Ge/Si self-assembled quantum dots. *Applied Physics Letters*, **2003**, 83, 2958-2960 | 3.4 | 53 |
| 134 | Diamagnetic response of exciton complexes in semiconductor quantum dots. *Physical Review Letters*, **2008**, 101, 267402 | 7.4 | 52 |
| 133 | Photoluminescence properties of self-assembled InN dots embedded in GaN grown by metal organic vapor phase epitaxy. *Applied Physics Letters*, **2006**, 88, 191913 | 3.4 | 51 |
| 132 | Bidirectional All-Optical Synapses Based on a 2D Bi2O2Se/Graphene Hybrid Structure for Multifunctional Optoelectronics. *Advanced Functional Materials*, **2020**, 30, 2001598 | 15.6 | 48 |
| 131 | Hole emission processes in InAs/GaAs self-assembled quantum dots. *Physical Review B*, **2002**, 66, | 3.3 | 43 |
| 130 | Large-Area 2D Layered MoTe2 by Physical Vapor Deposition and Solid-Phase Crystallization in a Tellurium-Free Atmosphere. *Advanced Materials Interfaces*, **2017**, 4, 1700157 | 4.6 | 41 |
| 129 | Ledge-directed epitaxy of continuously self-aligned single-crystalline nanoribbons of transition metal dichalcogenides. *Nature Materials*, **2020**, 19, 1300-1306 | 27 | 41 |
| 128 | Effects of thermal annealing on the emission properties of type-II InAs/GaAsSb quantum dots. *Applied Physics Letters*, **2009**, 94, 053101 | 3.4 | 38 |
| 127 | Carrier dynamics of type-II InAs□GaAs quantum dots covered by a thin GaAs1−xSbx layer. *Applied Physics Letters*, **2008**, 93, 033107 | 3.4 | 38 |
| 126 | Characterization of GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. *Journal of Applied Physics*, **2003**, 94, 1753-1757 | 2.5 | 35 |

| | | | |
|---|---|---|---|
| 125 | Quantum-confined Stark shift in electroreflectance of InAs/InxGa1−xAs self-assembled quantum dots. *Applied Physics Letters*, **2001**, 78, 1760-1762 | 3.4 | 33 |
| 124 | Investigations on diamond nanostructuring of different morphologies by the reactive-ion etching process and their potential applications. *ACS Applied Materials & Interfaces*, **2013**, 5, 7439-49 | 9.5 | 32 |
| 123 | Tailoring excitonic states of van der Waals bilayers through stacking configuration, band alignment, and valley spin. *Science Advances*, **2019**, 5, eaax7407 | 14.3 | 31 |
| 122 | Synthesis and structure of two-dimensional transition-metal dichalcogenides. *MRS Bulletin*, **2015**, 40, 566-576 | 3.2 | 30 |
| 121 | Moir potential impedes interlayer exciton diffusion in van der Waals heterostructures. *Science Advances*, **2020**, 6, | 14.3 | 29 |
| 120 | Metal-Guided Selective Growth of 2D Materials: Demonstration of a Bottom-Up CMOS Inverter. *Advanced Materials*, **2019**, 31, e1900861 | 24 | 28 |
| 119 | Layer-Dependent and In-Plane Anisotropic Properties of Low-Temperature Synthesized Few-Layer PdSe Single Crystals. *ACS Nano*, **2020**, 14, 4963-4972 | 16.7 | 28 |
| 118 | Large-area few-layer MoS2deposited by sputtering. *Materials Research Express*, **2016**, 3, 065007 | 1.7 | 28 |
| 117 | Effects of spacer thickness on optical properties of stacked Ge/Si quantum dots grown by chemical vapor deposition. *Journal of Applied Physics*, **2003**, 93, 4999-5002 | 2.5 | 28 |
| 116 | Anticorrelation between the splitting and polarization of the exciton fine structure in single self-assembled InAs/GaAs quantum dots. *Physical Review B*, **2011**, 83, | 3.3 | 27 |
| 115 | Impacts of structural asymmetry on the magnetic response of excitons and biexcitons in single self-assembled In(Ga)As quantum rings. *Physical Review B*, **2009**, 80, | 3.3 | 27 |
| 114 | Self-assembled free-standing colloidal crystals. *Nanotechnology*, **2005**, 16, 1440-1444 | 3.4 | 27 |
| 113 | Dielectric impact on exciton binding energy and quasiparticle bandgap in monolayer WS 2 and WSe 2. *2D Materials*, **2019**, 6, 025028 | 5.9 | 25 |
| 112 | Effects of GaAsSb capping layer thickness on the optical properties of InAs quantum dots. *Applied Physics Letters*, **2011**, 99, 073108 | 3.4 | 24 |
| 111 | Electroreflectance study on the polarization field in InGaN/AlInGaN multiple quantum wells. *Applied Physics Letters*, **2004**, 84, 1114-1116 | 3.4 | 24 |
| 110 | Single photon emission from an InGaAs quantum dot precisely positioned on a nanoplane. *Applied Physics Letters*, **2007**, 90, 073105 | 3.4 | 23 |
| 109 | Low-Threshold Plasmonic Lasers on a Single-Crystalline Epitaxial Silver Platform at Telecom Wavelength. *ACS Photonics*, **2017**, 4, 1431-1439 | 6.3 | 22 |
| 108 | Electroreflectance studies of InAs quantum dots with InxGa1−xAs capping layer grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2005**, 86, 131917 | 3.4 | 21 |

| | | | |
|---|---|---|---|
| 107 | Electron distribution and level occupation in an ensemble of InxGa1−xAs/GaAs self-assembled quantum dots. *Physical Review B*, **2000**, 62, 13040-13047 | 3.3 | 20 |
| 106 | Graphene-Au nanoparticle based vertical heterostructures: A novel route towards high- ZT Thermoelectric devices. *Nano Energy*, **2017**, 38, 385-391 | 17.1 | 19 |
| 105 | Strong coupling of different cavity modes in photonic molecules formed by two adjacent microdisk microcavities. *Optics Express*, **2010**, 18, 23948-56 | 3.3 | 19 |
| 104 | Time-resolved photoluminescence of isoelectronic traps in ZnSe1−xTex semiconductor alloys. *Applied Physics Letters*, **2008**, 93, 241909 | 3.4 | 19 |
| 103 | Designer germanium quantum dot phototransistor for near infrared optical detection and amplification. *Nanotechnology*, **2015**, 26, 055203 | 3.4 | 18 |
| 102 | Carrier dynamics in isoelectronic ZnSe1−xOx semiconductors. *Applied Physics Letters*, **2010**, 97, 041909 | 3.4 | 18 |
| 101 | Anomalous diamagnetic shift for negative trions in single semiconductor quantum dots. *Physical Review B*, **2010**, 81, | 3.3 | 18 |
| 100 | Optical fine structures of highly quantized InGaAs/GaAs self-assembled quantum dots. *Physical Review B*, **2010**, 81, | 3.3 | 18 |
| 99 | Optical control of the exciton charge states of single quantum dots via impurity levels. *Physical Review B*, **2005**, 72, | 3.3 | 18 |
| 98 | 1.55□m emission from InAs quantum dots grown on GaAs. *Applied Physics Letters*, **2005**, 87, 151903 | 3.4 | 18 |
| 97 | Impacts of ammonia background flows on structural and photoluminescence properties of InN dots grown on GaN by flow-rate modulation epitaxy. *Applied Physics Letters*, **2006**, 89, 263117 | 3.4 | 17 |
| 96 | Electron-filling modulation reflectance in charged self-assembled InxGa1−xAs quantum dots. *Physical Review B*, **1999**, 60, R2189-R2192 | 3.3 | 17 |
| 95 | Effect of donor-acceptor concentration ratios on nonradiative energy transfer in closely packed CdTe quantum dots. *Applied Physics Letters*, **2009**, 95, 133123 | 3.4 | 16 |
| 94 | Studies on the electronic and vibrational states of colloidal CdSe/ZnS quantum dots under high pressures. *Nanotechnology*, **2007**, 18, 185402 | 3.4 | 16 |
| 93 | Monolayer MoS2 Enabled Single-Crystalline Growth of AlN on Si(100) Using Low-Temperature Helicon Sputtering. *ACS Applied Nano Materials*, **2019**, 2, 1964-1969 | 5.6 | 15 |
| 92 | Effects of growth temperature on InN□GaN nanodots grown by metal organic chemical vapor deposition. *Journal of Applied Physics*, **2008**, 103, 104306 | 2.5 | 15 |
| 91 | Stress tuning of strong and weak couplings between quantum dots and cavity modes in microdisk microcavities. *Physical Review B*, **2011**, 84, | 3.3 | 14 |
| 90 | Optical properties associated with strain relaxations in thick InGaN epitaxial films. *Optics Express*, **2014**, 22 Suppl 2, A416-24 | 3.3 | 13 |

| | | | |
|---|---|---|---|
| 89 | Distance dependence of energy transfer from InGaN quantum wells to graphene oxide. *Optics Letters*, **2013**, 38, 2897-9 | 3 | 13 |
| 88 | Nonresonant carrier transfer in single InGaAs/GaAs quantum dot molecules. *Physical Review B*, **2008**, 77, | 3.3 | 13 |
| 87 | Atomic-Layer Controlled Interfacial Band Engineering at Two-Dimensional Layered PtSe/Si Heterojunctions for Efficient Photoelectrochemical Hydrogen Production. *ACS Nano*, **2021**, 15, 4627-4635 | 16.7 | 12 |
| 86 | Epitaxial Growth of Optically Thick, Single Crystalline Silver Films for Plasmonics. *ACS Applied Materials & Interfaces*, **2019**, 11, 3189-3195 | 9.5 | 12 |
| 85 | High On-State Current in Chemical Vapor Deposited Monolayer MoS2 nFETs With Sn Ohmic Contacts. *IEEE Electron Device Letters*, **2021**, 42, 272-275 | 4.4 | 12 |
| 84 | Distributed Bragg Reflectors as Broadband and Large-Area Platforms for Light-Coupling Enhancement in 2D Transition-Metal Dichalcogenides. *ACS Applied Materials & Interfaces*, **2018**, 10, 16874-16880 | 9.5 | 11 |
| 83 | Polymer-free patterning of graphene at sub-10-nm scale by low-energy repetitive electron beam. *Small*, **2014**, 10, 4778-84 | 11 | 11 |
| 82 | A study of the Franz□Keldysh oscillations in electromodulation reflectance of Si-delta-doped GaAs by a fast Fourier transformation. *Journal of Applied Physics*, **1998**, 83, 7873-7878 | 2.5 | 11 |
| 81 | Ultralow Schottky Barriers in Hexagonal Boron Nitride-Encapsulated Monolayer WSe Tunnel Field-Effect Transistors. *ACS Applied Materials & Interfaces*, **2020**, 12, 18667-18673 | 9.5 | 10 |
| 80 | Growth of sparse arrays of narrow GaN nanorods hosting spectrally stable InGaN quantum disks. *Optics Express*, **2012**, 20, 16166 | 3.3 | 10 |
| 79 | Impacts of coulomb interactions on the magnetic responses of excitonic complexes in single semiconductor nanostructures. *Nanoscale Research Letters*, **2010**, 5, 680-5 | 5 | 10 |
| 78 | Growth of low density InGaAs quantum dots for single photon sources by metal□organic chemical vapour deposition. *Nanotechnology*, **2006**, 17, 512-515 | 3.4 | 10 |
| 77 | Excitation Density and Temperature Dependent Photoluminescence of InGaAs Self-Assembled Quantum Dots. *Japanese Journal of Applied Physics*, **1999**, 38, 554-557 | 1.4 | 10 |
| 76 | Effect of focused ion beam deposition induced contamination on the transport properties of nano devices. *Nanotechnology*, **2015**, 26, 055705 | 3.4 | 9 |
| 75 | Growth of optical-quality, uniform In-rich InGaN films using two-heater metal-organic chemical vapor deposition. *Journal of Crystal Growth*, **2013**, 383, 106-111 | 1.6 | 9 |
| 74 | Linear photon up-conversion of 450 meV in InGaN/GaN multiple quantum wells via Mn-doped GaN intermediate band photodetection. *Optics Express*, **2011**, 19 Suppl 6, A1211-8 | 3.3 | 9 |
| 73 | Optical properties of stacked Ge/Si quantum dots with different spacer thickness grown by chemical vapor deposition. *Applied Surface Science*, **2004**, 224, 148-151 | 6.7 | 9 |
| 72 | Suppressed piezoelectric polarization in single InGaN/GaN heterostructure nanowires. *Physical Review B*, **2013**, 88, | 3.3 | 8 |

| | | | |
|---|---|---|---|
| 71 | Recombination dynamics and carrier lifetimes in highly mismatched ZnTeO alloys. *Applied Physics Letters*, **2013**, 103, 261905 | 3.4 | 8 |
| 70 | Efficient energy transfer from InGaN quantum wells to Ag nanoparticles. *Physical Chemistry Chemical Physics*, **2013**, 15, 3618-22 | 3.6 | 8 |
| 69 | Enhanced light emission from InAs quantum dots in single-defect photonic crystal microcavities at room temperature. *Applied Physics Letters*, **2005**, 87, 071111 | 3.4 | 8 |
| 68 | Temperature-dependent optical and vibrational properties of PtSe thin films. *Scientific Reports*, **2020**, 10, 19003 | 4.9 | 8 |
| 67 | Atomic scale depletion region at one dimensional MoSe2-WSe2 heterointerface. *Applied Physics Letters*, **2018**, 113, 241601 | 3.4 | 8 |
| 66 | Effects of oxygen bonding on defective semiconducting and metallic single-walled carbon nanotube bundles. *Carbon*, **2012**, 50, 4619-4627 | 10.4 | 7 |
| 65 | Memory device application of wide-channel in-plane gate transistors with type-II GaAsSb-capped InAs quantum dots. *Applied Physics Letters*, **2013**, 103, 143502 | 3.4 | 7 |
| 64 | Recombination lifetimes in InN films studied by time-resolved excitation-correlation spectroscopy. *Physical Review B*, **2009**, 80, | 3.3 | 7 |
| 63 | Pressure-induced metallization and resonant Raman scattering in Zn1−xMnxTe. *Journal of Applied Physics*, **2008**, 104, 013503 | 2.5 | 7 |
| 62 | Structural and optical properties of In-rich InGaN nanodots grown by metallo-organic chemical vapor deposition. *Nanotechnology*, **2007**, 18, 405305 | 3.4 | 7 |
| 61 | Enhancing luminescence efficiency of InAs quantum dots at 1.5 μm using a carrier blocking layer. *Applied Physics Letters*, **2006**, 89, 053110 | 3.4 | 7 |
| 60 | Band alignment tuning of InAs quantum dots with a thin AlGaAsSb capping layer. *Applied Physics Letters*, **2013**, 102, 173104 | 3.4 | 6 |
| 59 | A Carrier Escape Study from InAs Self-Assembled Quantum Dots by Photocurrent Measurement. *Physica Status Solidi (B): Basic Research*, **2001**, 224, 85-88 | 1.3 | 6 |
| 58 | Growth and optical properties of high-density InN nanodots. *Journal of Crystal Growth*, **2010**, 312, 3209-3213 | 1.8 | 5 |
| 57 | Raman scattering of longitudinal-optical-phonon-plasmon coupling in Cl-doped ZnSe under high pressure. *Journal of Applied Physics*, **2007**, 102, 123510 | 2.5 | 5 |
| 56 | Room temperature 1.3 and 1.5 μm electroluminescence from Si/Ge quantum dots (QDs)/Si multi-layers. *Applied Surface Science*, **2004**, 224, 165-169 | 6.7 | 5 |
| 55 | Fast Fourier transformation of piezoreflectance in δ-doped GaAs. *Journal of Applied Physics*, **1998**, 84, 1074-1080 | 2.5 | 5 |
| 54 | Ultrafast Exciton Trapping and Exciton−Exciton Annihilation in Large-Area CVD-Grown Monolayer WS2. *Journal of Physical Chemistry C*, | 3.8 | 5 |

| | | | |
|---|---|---|---|
| 53 | Time-resolved ARPES Determination of a Quasi-Particle Band Gap and Hot Electron Dynamics in Monolayer MoS. *Nano Letters*, **2021**, 21, 7363-7370 | 11.5 | 5 |
| 52 | Cross-plane thermoelectric figure of merit in graphene - C60 heterostructures at room temperature. *FlatChem*, **2019**, 14, 100089 | 5.1 | 4 |
| 51 | Effect of Electrode Shape on Impedance of Single HeLa Cell: A COMSOL Simulation. *BioMed Research International*, **2015**, 2015, 871603 | 3 | 4 |
| 50 | Stacking fault induced tunnel barrier in platelet graphite nanofiber. *Applied Physics Letters*, **2014**, 105, 103505 | 3.4 | 4 |
| 49 | In-Plane Gate Transistors for Photodetector Applications. *IEEE Electron Device Letters*, **2013**, 34, 780-782 | 4.4 | 4 |
| 48 | Size-dependent strain relaxation in InN islands grown on GaN by metalorganic chemical vapor deposition. *Applied Physics Letters*, **2009**, 94, 063102 | 3.4 | 4 |
| 47 | Optical properties of Mn in regrown GaN-based epitaxial layers. *Optical Materials Express*, **2012**, 2, 469 | 2.6 | 4 |
| 46 | DC Characteristics of InAlAs/InGaAsSb/InGaAs Double Heterojunction Bipolar Transistors. *IEEE Transactions on Electron Devices*, **2010**, 57, 3327-3332 | 2.9 | 4 |
| 45 | Tailoring of the Wave Function Overlaps and the Carrier Lifetimes in InAs/GaAs1□Sbx Type-II Quantum Dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2010**, 42, 2524-2528 | 3 | 4 |
| 44 | Atomic-Step-Induced Screw-Dislocation-Driven Spiral Growth of SnS. *Chemistry of Materials*, **2021**, 33, 186-194 | 9.6 | 4 |
| 43 | Efficient modulation of subwavelength focusing via meta-aperture-based plasmonic lens for multifunction applications. *Scientific Reports*, **2018**, 8, 13648 | 4.9 | 4 |
| 42 | Hybrid Composites of Quantum Dots, Monolayer WSe2, and Ag Nanodisks for White Light-Emitting Diodes. *ACS Applied Nano Materials*, **2020**, 3, 6855-6862 | 5.6 | 3 |
| 41 | Energy transfer from InGaN quantum wells to Au nanoclusters via optical waveguiding. *Optics Express*, **2011**, 19 Suppl 2, A194-200 | 3.3 | 3 |
| 40 | The structural and optical properties of InN nanodots grown with various V/III ratios by metal-organic chemical vapor deposition. *Nanotechnology*, **2009**, 20, 295702 | 3.4 | 3 |
| 39 | Time-resolved photoluminescence of type-II InAs/GaAs quantum dots covered by a thin GaAs1□Sbx layer. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 1449-1452 | | 3 |
| 38 | Optical Properties of Uncapped InN Nanodots Grown at Various Temperatures. *Japanese Journal of Applied Physics*, **2009**, 48, 031001 | 1.4 | 3 |
| 37 | Two-dimensional solid-phase crystallization toward centimeter-scale monocrystalline layered MoTe2via two-step annealing. *Journal of Materials Chemistry C*, | 7.1 | 3 |
| 36 | Room-Temperature Ferromagnetism of Single-Layer MoS2 Induced by Antiferromagnetic Proximity of Yttrium Iron Garnet. *Advanced Quantum Technologies*, **2021**, 4, 2000104 | 4.3 | 3 |

| | | | |
|---|---|---|---|
| 35 | Low temperature deposition of high quality single crystalline AlN thin films on sapphire using highly oriented monolayer MoS2 as a buffer layer. *Journal of Crystal Growth*, **2020**, 544, 125726 | 1.6 | 3 |
| 34 | Strain-Directed Layer-By-Layer Epitaxy Toward van der Waals Homo- and Heterostructures **2021**, 3, 442-453 | | 3 |
| 33 | Three-Dimensional Resolvable Plasmonic Concentric Compound Lens: Approaching the Axial Resolution from Microscale to Nanoscale. *ACS Photonics*, **2018**, 5, 834-843 | 6.3 | 3 |
| 32 | Design of multifold Ge/Si/Ge composite quantum-dot heterostructures for visible to near-infrared photodetection. *Optics Letters*, **2015**, 40, 2401-4 | 3 | 2 |
| 31 | Nitride-stressor and quantum-size engineering in Ge quantum-dot photoluminescence wavelength and exciton lifetime. *Nano Futures*, **2020**, 4, 015001 | 3.6 | 2 |
| 30 | Synthesis of SiV-diamond particulates via the microwave plasma chemical deposition of ultrananocrystalline diamond on soda-lime glass fibers. *Materials Research Express*, **2016**, 3, 106205 | 1.7 | 2 |
| 29 | Determination of s-d exchange coupling in GaMnN by time-resolved Kerr rotation spectroscopy. *Physical Review B*, **2014**, 90, | 3.3 | 2 |
| 28 | Temperature-dependent decay dynamics in highly mismatched ZnSe1−xTex alloy. *Applied Physics Letters*, **2012**, 100, 071912 | 3.4 | 2 |
| 27 | Analysis of electrode shape effect on single HeLa cell impedance using COMSOL simulation **2013**, | | 2 |
| 26 | Optical characterization of isoelectronic ZnSe1−xOx semiconductors. *Journal of Crystal Growth*, **2011**, 323, 122-126 | 1.6 | 2 |
| 25 | Origins of nonzero multiple photon emission probability from single quantum dots embedded in photonic crystal nanocavities. *Applied Physics Letters*, **2009**, 94, 163111 | 3.4 | 2 |
| 24 | Structural and optical properties of indium-rich InGaN islands. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1702-1705 | | 2 |
| 23 | Structural and optical properties of InN/GaN nanodots grown by metalorganic chemical vapor deposition. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 3014-3016 | | 2 |
| 22 | Effect of ZnSe partial capping on the ripening dynamics of CdSe quantum dots. *Applied Physics Letters*, **2007**, 90, 083116 | 3.4 | 2 |
| 21 | Optical emission from individual InGaAs quantum dots in single-defect photonic crystal nanocavity. *Journal of Applied Physics*, **2005**, 98, 034306 | 2.5 | 2 |
| 20 | Effects of Electric Field and Coulomb Interaction on the Interband Transitions of InAs Self-Assembled Quantum Dots: A Study by Modulation Reflectance Spectroscopy. *Physica Status Solidi (B): Basic Research*, **2001**, 224, 89-92 | 1.3 | 2 |
| 19 | Grain size effect of monolayer MoS2 transistors characterized by second harmonic generation mapping **2015**, | | 1 |
| 18 | Original method of GaN and InGaN quantum dots formation on (0001)AlN surface by ammonia molecular beam epitaxy. *Journal of Physics: Conference Series*, **2017**, 864, 012007 | 0.3 | 1 |

| | | | |
|---|---|---|---|
| 17 | Optical detection of anisotropicg-factor and nuclear spin polarization in a single CdTe quantum well. *Japanese Journal of Applied Physics*, **2015**, 54, 033003 | 1.4 | 1 |
| 16 | Magneto-optical properties of ZnMnTe/ZnSe quantum dots. *Journal of Crystal Growth*, **2011**, 323, 380-382 | 1.6 | 1 |
| 15 | Cathodoluminescence studies of GaAs nano-wires grown on shallow-trench-patterned Si. *Nanotechnology*, **2010**, 21, 465701 | 3.4 | 1 |
| 14 | Carrier gas effects on the SiGe quantum dots formation. *Applied Surface Science*, **2008**, 254, 6257-6260 | 6.7 | 1 |
| 13 | Scanning electron filling modulation reflectance of charged InGaAs self-assembled quantum dot. *Journal of Applied Physics*, **2002**, 91, 4399-4402 | 2.5 | 1 |
| 12 | Momentum-Resolved Electronic Structures of a Monolayer-MoS2/Multilayer-MoSe2 Heterostructure. *Journal of Physical Chemistry C*, **2021**, 125, 16591-16597 | 3.8 | 1 |
| 11 | Influences of Contact Metals on the Performances of MoS2 Devices under Strains. *Journal of Physical Chemistry C*, **2019**, 123, 30696-30703 | 3.8 | 1 |
| 10 | Ultrafast laser ablation, intrinsic threshold, and nanopatterning of monolayer molybdenum disulfide.. *Scientific Reports*, **2022**, 12, 6910 | 4.9 | 1 |
| 9 | 2D Materials: Metal-Guided Selective Growth of 2D Materials: Demonstration of a Bottom-Up CMOS Inverter (Adv. Mater. 18/2019). *Advanced Materials*, **2019**, 31, 1970132 | 24 | 0 |
| 8 | Fabrication of Large-Scale High-Mobility Flexible Transparent Zinc Oxide Single Crystal Wafers. *ACS Applied Materials & Interfaces*, **2021**, 13, 18991-18998 | 9.5 | 0 |
| 7 | Diffraction-Unlimited Plasmonic Nanolaser. *Topics in Applied Physics*, **2015**, 357-359 | 0.5 | |
| 6 | Waveguide based energy transfer with gold nanoclusters for detection of hydrogen peroxide. *RSC Advances*, **2014**, 4, 30392-30397 | 3.7 | |
| 5 | Exciton fine structures and energy transfer in single InGaAs quantum-dot molecules. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 860-863 | | |
| 4 | Electron–hole symmetry breakings in optical fine structures of single self-assembled quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2010**, 42, 1155-1158 | 3 | |
| 3 | Ultrafast multi-shot ablation and defect generation in monolayer transition metal dichalcogenides. *AIP Advances*, **2022**, 12, 015217 | 1.5 | |
| 2 | Investigation of the spectral characteristics of silicon-vacancy centers in ultrananocrystalline diamond nanostructures and single crystalline diamond. *Journal of Applied Physics*, **2020**, 127, 035302 | 2.5 | |
| 1 | In Situ Atomic-Scale Observation of Monolayer MoS 2 Devices under High-Voltage Biasing via Transmission Electron Microscopy (Small 7/2022). *Small*, **2022**, 18, 2270034 | 11 | |